Henryk Turski

List of Publications by Year
in descending order

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80 papers	969 citations	471371 17 h-index	580701 25 g-index
88 all docs	88 docs citations	88 times ranked	715 citing authors

#	Article	IF	Citations
1	III-nitride optoelectronic devices containing wide quantum wellsâ€"unexpectedly efficient light sources. Japanese Journal of Applied Physics, 2022, 61, SA0801.	0.8	14
2	Electrically pumped blue laser diodes with nanoporous bottom cladding. Optics Express, 2022, 30, 10709.	1.7	6
3	Electrical transport properties of highly doped N-type GaN materials. Semiconductor Science and Technology, 2022, 37, 055012.	1.0	6
4	Dependence of InGaN Quantum Well Thickness on the Nature of Optical Transitions in LEDs. Materials, 2022, 15, 237.	1.3	13
5	Bottom tunnel junction-based blue LED with a thin Ge-doped current spreading layer. Applied Physics Letters, 2022, 120, 171104.	1.5	1
6	Ion implantation of tunnel junction as a method for defining the aperture of III-nitride-based micro-light-emitting diodes. Optics Express, 2022, 30, 27004.	1.7	7
7	Tunnel Junctions with a Doped (<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML") Tj ETQq1 1 0.784314 rgBT /Overlock mathvariant="normal">N</mml:mi></mml:mrow></mml:mrow></mml:math> Quantum Well for Vertical Integration of <i>III</i> -Nitride Optoelectronic Devices. Physical Review Applied, 2021, 15, .	1.5	11
8	Role of Metal Vacancies in the Mechanism of Thermal Degradation of InGaN Quantum Wells. ACS Applied Materials & Interfaces, 2021, 13, 7476-7484.	4.0	15
9	Free Excitonic Emission in Homoepitaxial Layers Grown on Bulk GaN Substrates. Acta Physica Polonica A, 2021, 139, 300-303.	0.2	0
10	Enhanced efficiency in bottom tunnel junction InGaN blue LEDs. , 2021, , .		6
11	Composition Inhomogeneity in Nonpolar (101Ì...0) and Semipolar (202Ì...1) InAlN Layers Grown by Plasma-Assisted Molecular Beam Epitaxy. Crystal Growth and Design, 2021, 21, 5223-5230.	1.4	1
12	Dislocation and indium droplet related emission inhomogeneities in InGaN LEDs. Journal Physics D: Applied Physics, 2021, 54, 495106.	1.3	6
13	Optical properties of N-polar GaN: The possible role of nitrogen vacancy-related defects. Applied Surface Science, 2021, 566, 150734.	3.1	8
14	Quantum-confined Stark effect and mechanisms of its screening in InGaN/GaN light-emitting diodes with a tunnel junction. Optics Express, 2021, 29, 1824.	1.7	20
15	Influence of Growth Polarity Switching on the Optical and Electrical Properties of GaN/AlGaN Nanowire LEDs. Electronics (Switzerland), 2021, 10, 45.	1.8	3
16	Nitride LEDs and Lasers with Buried Tunnel Junctions. ECS Journal of Solid State Science and Technology, 2020, 9, 015018.	0.9	12
17	Vertical Integration of Nitride Laser Diodes and Light Emitting Diodes by Tunnel Junctions. Electronics (Switzerland), 2020, 9, 1481.	1.8	17
18	III-N/Siâ‚ƒNâ‚„ Integrated Photonics Platform for Blue Wavelengths. IEEE Journal of Quantum Electronics, 2020, 56, 1-9.	1.0	8

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19	Inhomogeneous broadening of optical transitions observed in photoluminescence and modulated reflectance of polar and non-polar InGaN quantum wells. Journal of Applied Physics, 2020, 127, 035702.	1.1	1
20	Revealing inhomogeneous Si incorporation into GaN at the nanometer scale by electrochemical etching. Nanoscale, 2020, 12, 6137-6143.	2.8	11
21	Gallium nitride tunneling field-effect transistors exploiting polarization fields. Applied Physics Letters, 2020, 116, .	1.5	7
22	Stacking faults in plastically relaxed InGaN epilayers. Semiconductor Science and Technology, 2020, 35, 034003.	1.0	5
23	Monolithically p-down nitride laser diodes and LEDs obtained by MBE using buried tunnel junction design. , 2020, , .		2
24	Enhanced injection efficiency and light output in bottom tunnel-junction light-emitting diodes. Optics Express, 2020, 28, 4489.	1.7	19
25	Nitride light-emitting diodes for cryogenic temperatures. Optics Express, 2020, 28, 30299.	1.7	8
26	Distributed-feedback blue laser diode utilizing a tunnel junction grown by plasma-assisted molecular beam epitaxy. Optics Express, 2020, 28, 35321.	1.7	9
27	Beyond Quantum Efficiency Limitations Originating from the Piezoelectric Polarization in Light-Emitting Devices. ACS Photonics, 2019, 6, 1963-1971.	3.2	33
28	Polarization control in nitride quantum well light emitters enabled by bottom tunnel-junctions. Journal of Applied Physics, 2019, 125, 203104.	1.1	24
29	Optical properties of III-nitride laser diodes with wide InGaN quantum wells. Applied Physics Express, 2019, 12, 072003.	1.1	16
30	Unusual step meandering due to Ehrlich-Schwoebel barrier in GaN epitaxy on the N-polar surface. Applied Surface Science, 2019, 484, 771-780.	3.1	22
31	Nitrogen-rich growth for device quality N-polar InGaN/GaN quantum wells by plasma-assisted MBE. Journal of Crystal Growth, 2019, 512, 208-212.	0.7	5
32	Tunnel junctions for vertically integrated multiple nitrides laser diodes. , 2019, , .		0
33	Buried tunnel junction for p-down nitride laser diodes. , 2019, , .		0
34	Extremely long lifetime of III-nitride laser diodes grown by plasma assisted molecular beam epitaxy. Materials Science in Semiconductor Processing, 2019, 91, 387-391.	1.9	9
35	Sensitivity of N-polar GaN surface barrier to ambient gases. Sensors and Actuators B: Chemical, 2019, 281, 561-567.	4.0	9
36	Stack of two III-nitride laser diodes interconnected by a tunnel junction. Optics Express, 2019, 27, 5784.	1.7	32

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37	Hydrogen diffusion in GaN:Mg and GaN:Si. Journal of Alloys and Compounds, 2018, 747, 354-358.	2.8	24
38	Luminescent N-polar (In,Ga)N/GaN quantum wells achieved by plasma-assisted molecular beam epitaxy at temperatures exceeding 700â€‰Â°C. Applied Physics Letters, 2018, 112, .	1.5	13
39	Growth rate independence of Mg doping in GaN grown by plasma-assisted MBE. Journal of Crystal Growth, 2018, 482, 56-60.	0.7	10
40	Tunnel junctions for two-color nitride light emitting diodes and laser diodes grown by plasma assisted molecular beam epitaxy. , 2018, , .		0
41	True-blue laser diodes with tunnel junctions grown monolithically by plasma-assisted molecular beam epitaxy. Applied Physics Express, 2018, 11, 034103.	1.1	39
42	Realization of the First GaN Based Tunnel Field-Effect Transistor. , 2018, , .		1
43	Miscut dependent surface evolution in the process of N-polar <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" altimg="si0021.gif" overflow="scroll"><mml:mi>GaN</mml:mi><mml:mo>(</mml:mo><mml:mn>000</mml:mn><mml:mover) Tj ETQq1 1 0.784314 rgBT /C	1.1	3
44	Comparative study of semipolar<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" altimg="si1.gif" overflow="scroll"><mml:mrow><mml:mo stretchy="false">(</mml:mo><mml:mn>2</mml:mn><mml:mspace width="0.12em") Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50 467 Td (/><r ... 2017, 457, 38-45.	0.7	6
45	Indium incorporation in semipolar <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" altimg="si0010.gif" overflow="scroll"><mml:mrow><mml:mo		

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55	AlGaN cladding-free 482 nm continuous wave nitride laser diodes grown by plasma-assisted molecular beam epitaxy. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2014, 32, 02C112.	0.6	0
56	Cyan laser diode grown by plasma-assisted molecular beam epitaxy. Applied Physics Letters, 2014, 104, 023503.	1.5	11
57	Trueâ€blue laser diodes grown by plasmaâ€assisted MBE on bulk GaN substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 666-669.	0.8	3
58	Nitride-based laser diodes grown by plasma-assisted molecular beam epitaxy. Journal Physics D: Applied Physics, 2014, 47, 073001.	1.3	56
59	Nitride-based laser diodes and superluminescent diodes. Photonics Letters of Poland, 2014, 6, .	0.2	3
60	Determination of gain in AlGaN cladding free nitride laser diodes. Applied Physics Letters, 2013, 103, .	1.5	14
61	Role of nonequivalent atomic step edges in the growth of InGaN by plasma-assisted molecular beam epitaxy. Proceedings of SPIE, 2013, , .	0.8	2
62	True-blue nitride laser diodes grown by plasma assisted MBE on low dislocation density GaN substrates. Proceedings of SPIE, 2013, , .	0.8	0
63	Step-flow growth mode instability of N-polar GaN under N-excess. Applied Physics Letters, 2013, 103, .	1.5	15
64	Growth mechanisms in semipolar <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" altimg="si0020.gif" overflow="scroll"><mml:mo stretchy="false">(</mml:mo><mml:mn>2</mml:mn><mml:mspace width=".5em") Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50 387 Td (/><mm <mml	0.7	20
65	Ultraviolet light-emitting diodes grown by plasma-assisted molecular beam epitaxy on semipolar GaN (202Â¯1) substrates. Applied Physics Letters, 2013, 102, .	1.5	9
66	Nonequivalent atomic step edgesâ€"Role of gallium and nitrogen atoms in the growth of InGaN layers. Journal of Crystal Growth, 2013, 367, 115-121.	0.7	46
67	Ultraviolet laser diodes grown on semipolar (202Â¯1) GaN substrates by plasma-assisted molecular beam epitaxy. Applied Physics Letters, 2013, 102, .	1.5	13
68	MBE fabrication of III-N-based laser diodes and its development to industrial system. Journal of Crystal Growth, 2013, 378, 278-282.	0.7	16
69	Investigation on the origin of luminescence quenching in N-polar (In,Ga)N multiple quantum wells. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2013, 31, .	0.6	15
70	Role of Nonequivalent Atomic Step Edges in the Growth of InGaN by Plasma-Assisted Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 2013, 52, 08JE02.	0.8	4
71	True-Blue Nitride Laser Diodes Grown by Plasma-Assisted Molecular Beam Epitaxy. Applied Physics Express, 2012, 5, 112103.	1.1	17
72	AlGaN-Free Laser Diodes by Plasma-Assisted Molecular Beam Epitaxy. Applied Physics Express, 2012, 5, 022104.	1.1	16

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73	InGaN laser diodes operating at 450â€“460 nm grown by rf-plasma MBE. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2012, 30, 02B102.	0.6	17
74	Waveguide Design for Long Wavelength InGaN Based Laser Diodes. Acta Physica Polonica A, 2012, 122, 1031-1033.	0.2	11
75	Growth mechanism of InGaN by plasma assisted molecular beam epitaxy. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2011, 29, 03C136.	0.6	25
76	Optically pumped 500 nm InGaN green lasers grown by plasma-assisted molecular beam epitaxy. Journal of Applied Physics, 2011, 110, .	1.1	44
77	High quality m-plane GaN grown under nitrogen-rich conditions by plasma assisted molecular beam epitaxy. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2011, 29, .	0.6	9
78	Step-flow anisotropy of the<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mi>m</mml:mi></mml:mrow></mml:math>-plane GaN (<mml:math) Tj ETQq0 0 0 rgBT /Overlock 1 grown under nitrogen-rich conditions by plasma-assisted molecular beam epitaxy. Physical Review B, 2	1.1	20
79	InAlGaN laser diodes grown by plasma assisted molecular beam epitaxy. Lithuanian Journal of Physics, 2011, 51, 276-282.	0.1	1
80	Magnetic Liquid Crystals for Molecular Spintronics. Acta Physica Polonica A, 2008, 114, 1383-1386.	0.2	0